

EMIF02-MIC02F1

2 LINES EMI FILTER AND ESD PROTECTION

$IPAD^{TM}$

MAIN PRODUCT CHARACTERISTICS:

Where EMI filtering in ESD sensitive equipment is required:

- Mobile phones and communication systems
- Computers, printers and MCU Boards

DESCRIPTION

The EMIF02-MIC02 is a highly integrated devices designed to suppress EMI/RFI noise in all systems subjected to electromagnetic interferences. The EMIF02 flip chip packaging means the package size is equal to the die size.

This filter includes an ESD protection circuitry which prevents the device from destruction when subjected to ESD surges up 15kV.

BENEFITS

- EMI symmetrical (I/O) low-pass filter
- High efficiency in EMI filtering
- Very low PCB space consuming: 1.07mm x 1.57mm
- Very thin package: 0.65 mm
- High efficiency in ESD suppression
- High reliability offered by monolithic integration
- High reducing of parasitic elements through integration & wafer level packaging.

COMPLIES WITH THE FOLLOWING STANDARDS: IEC61000-4-2

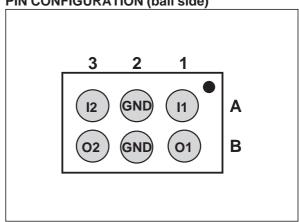
Level 4 on input pins 15kV (air discharge) 8 kV (contact discharge) 2kV Level 1 on output pins (air discharge)

> 2kV (contact discharge)

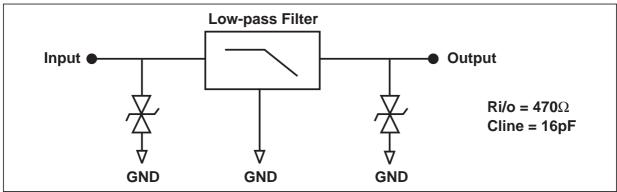
MIL STD 883E - Method 3015-6 Class 3

Flip Chip package

PIN CONFIGURATION (ball side)



BASIC CELL CONFIGURATION



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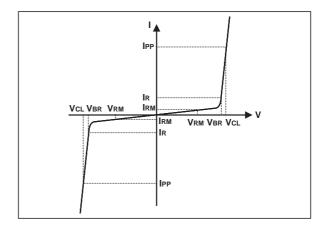
EMIF02-MIC02F1

ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter and test conditions | Value | Unit |
|------------------|-------------------------------|-------------|------|
| T _j | Maximum junction temperature | 125 | °C |
| T _{op} | Operating temperature range | -40 to + 85 | °C |
| T _{stg} | Storage temperature range | -55 to 150 | °C |

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C)

| Symbol | Parameter |
|-------------------|--|
| V _{BR} | Breakdown voltage |
| I _{RM} | Leakage current @ V _{RM} |
| V _{RM} | Stand-off voltage |
| V _{CL} | Clamping voltage |
| R _d | Dynamic impedance |
| I _{PP} | Peak pulse current |
| R _{I/O} | Series resistance between Input & Output |
| C _{line} | Input capacitance per line |



| Symbol | Test conditions | Min. | Тур. | Max. | Unit |
|-------------------|--------------------------------|------|------|------|------|
| V_{BR} | I _R = 1 mA | 14 | 16 | | V |
| I _{RM} | V _{RM} = 12V per line | | | 500 | nA |
| R _{I/O} | | 423 | 470 | 517 | Ω |
| C _{line} | @ 0V | | 16 | | pF |

Fig. 1: S21(dB) attenuation measurement and Aplac simulation.

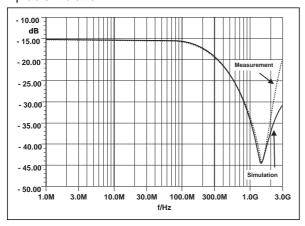
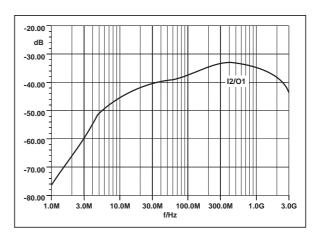


Fig. 2: Analog crosstalk measurements.



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Fig. 3: Digital crosstalk measurement.

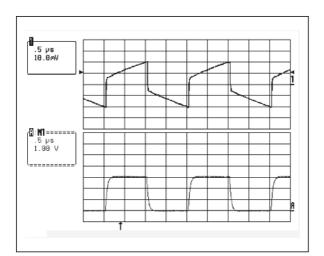


Fig. 5: ESD response to IEC61000-4-2 (-15kV air discharge) on one input V(in) and on one output (Vout).

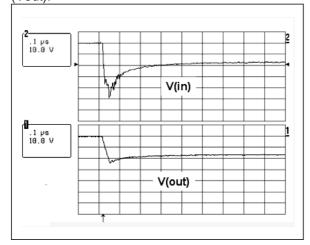


Fig. 4: ESD response to IEC61000-4-2 (+15kV air discharge) on one input V(in) and on one output (Vout).

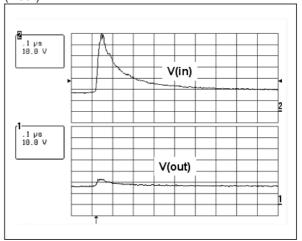
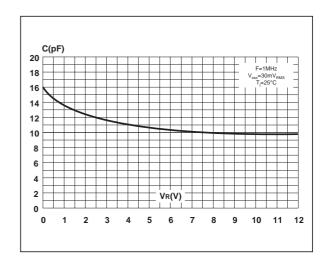


Fig. 6: Line capacitance versus applied voltage.



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Fig. 7: Aplac model.

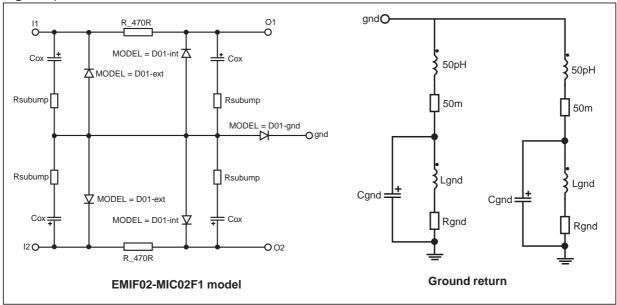
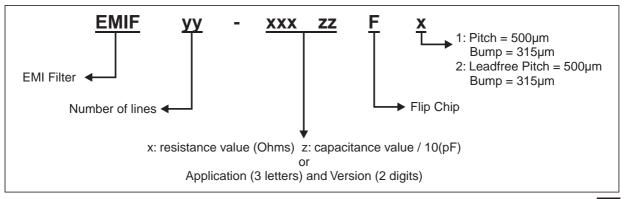


Fig. 8: Aplac parameters.

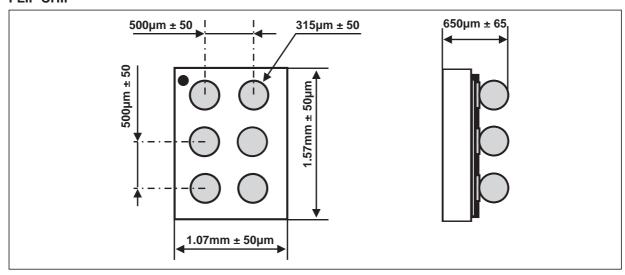
| Model D01-ext BV = 7 CJO = Cz_ext | Model D01-int BV = 7 CJO = Cz_int | Model D01-gnd BV = 7 CJO = Cz_gnd | aplacvar Ls 400pH aplacvar Rs 100m |
|--|--|--|--|
| IBV = 1u IKF = 1000 IS = 10f ISR = 100p N = 1 M = 0.3333 RS = Rs ext | IBV = 1u IKF = 1000 IS = 10f ISR = 100p N = 1 M = 0.3333 RS = Rs int | IBV = 1u IKF = 1000 IS = 10f ISR = 100p N = 1 M = 0.3333 RS = Rs_gnd | aplacvar R_470R 482.6 aplacvar Cz_ext 8.73pF aplacvar Rs_ext 850m aplacvar Cz_int 2.9pF aplacvar Rs_int 850m aplacvar Cz_gnd 215.61pF aplacvar Rs_gnd 470m |
| VJ = 0.6 TT = 50n | VJ = 0.6 TT = 50n | VJ = 0.6 TT = 50n | aplacvar Rgnd 10m aplacvar Lgnd 48pH aplacvar Cgnd 0.15pF aplacvar Cox 3.05pF aplacvar Rsubump 200m |

ORDER CODE

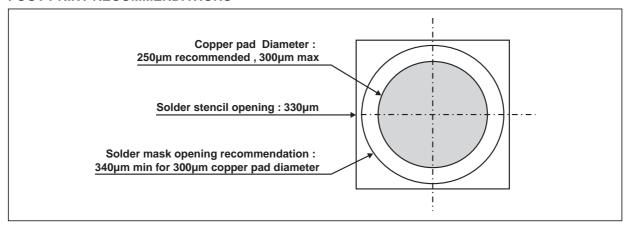


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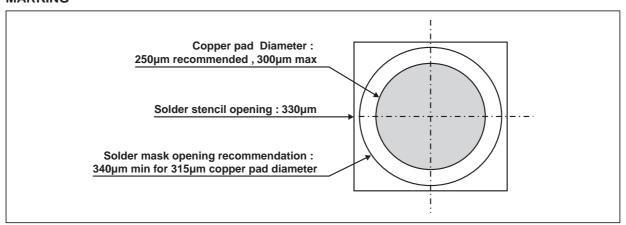
PACKAGE MECHANICAL DATA FLIP CHIP



FOOT PRINT RECOMMENDATIONS

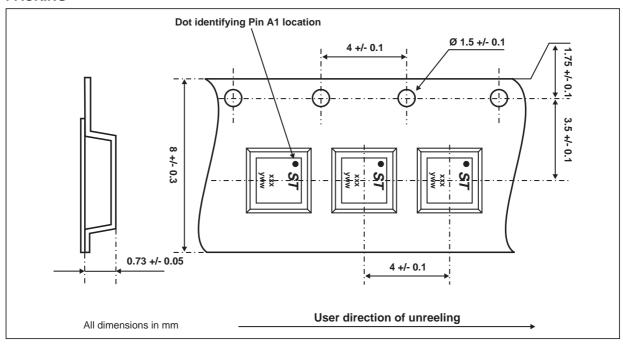


MARKING



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PACKING



OTHER INFORMATION

| Ordering code | Marking | Package | Weight | Base qty | Delivery mode |
|----------------|---------|-----------|--------|----------|------------------|
| EMIF02-MIC02F1 | FJT | Flip Chip | 2.3 mg | 5000 | Tape & reel (7") |

Note: More packing informations are available in the application note AN1235: "Flip-Chip: Package description and recommandations for use"

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